



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

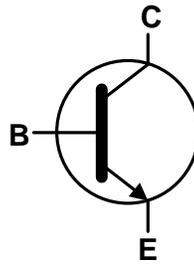
- $BV_{CEO} > 40V$
- $I_C = 200mA$ Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary PNP Type: NK-MMST3906Q

Mechanical Data

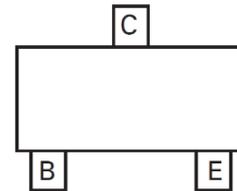
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



Pin-out Top View

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	I _C	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

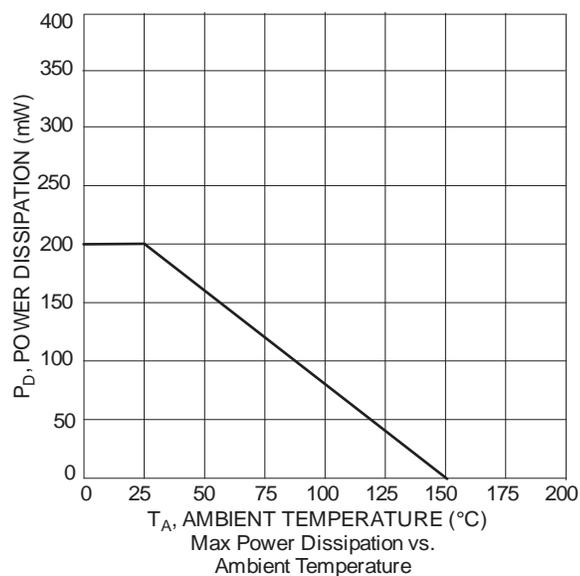
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

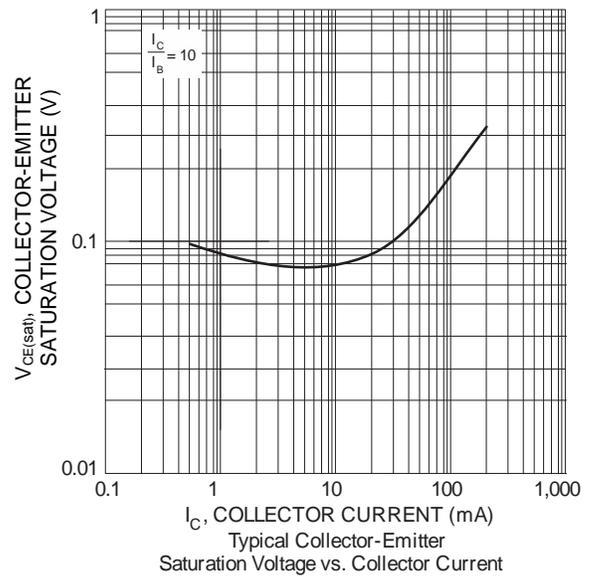
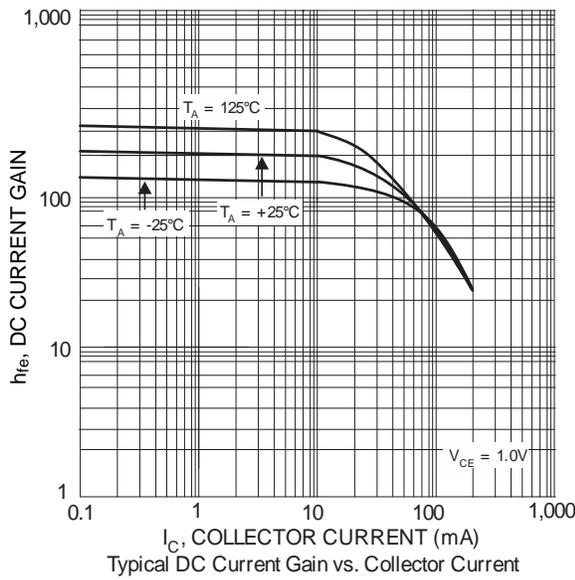
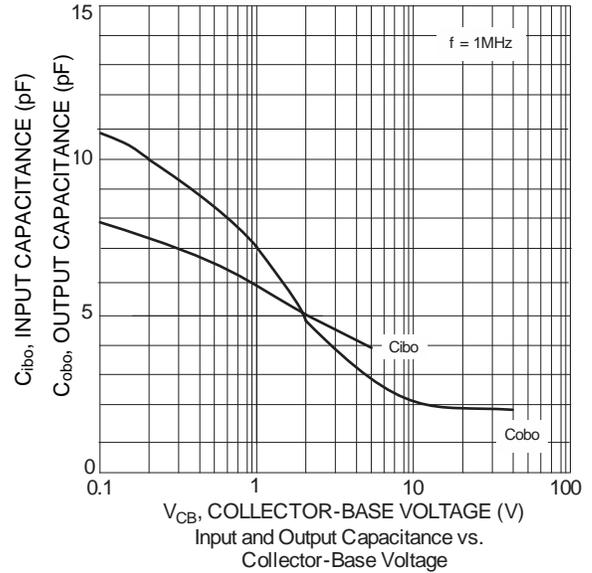
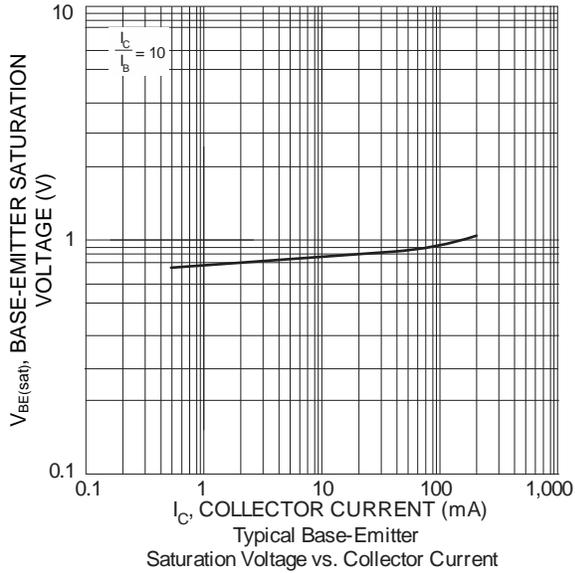


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV _{CB0}	60	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	—	V	I _C = 1mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EB0}	5	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CEX}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3V
Base Cutoff Current	I _{BL}	—	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3V
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h _{FE}	40	—	—	I _C = 100μA, V _{CE} = 1V
		70	—		
		100	300		
		60	—		
		30	—		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	0.25 0.30	V	I _C = 10mA, I _B = 1mA I _C = 50mA, I _B = 5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.65 —	0.85 0.95	V	I _C = 10mA, I _B = 1mA I _C = 50mA, I _B = 5mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4	pF	V _{CB} = 5V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	8	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	1	10	kΩ	V _{CE} = 10V, I _C = 1mA, f = 1.0MHz
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	
Small Signal Current Gain	h _{fe}	100	400	—	
Output Admittance	h _{oe}	1	40	μS	
Current Gain-Bandwidth Product	f _T	300	—	MHz	
Noise Figure	NF	—	5	dB	V _{CC} = 5V, I _C = 100μA, R _S = 1kΩ, f = 1MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	35	ns	V _{CC} = 3V, I _C = 10mA,
Rise Time	t _r	—	35	ns	V _{BE(OFF)} = -0.5V, I _{B1} = 1mA
Storage Time	t _s	—	200	ns	V _{CC} = 3.0V, I _C = 10mA,
Fall Time	t _f	—	50	ns	I _{B1} = I _{B2} = 1.0mA

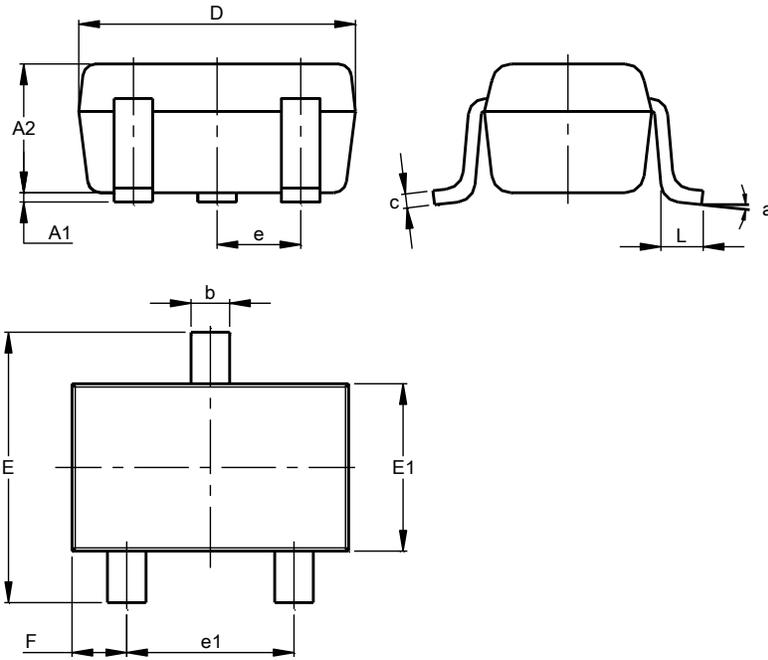
Notes: 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

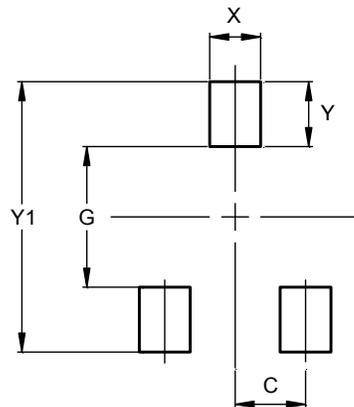
SOT323



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500